



30V/112A N-Channel Advanced Power MOSFET

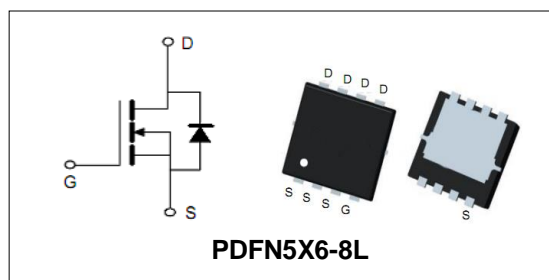
Features

- Low RDS(on)@4.5V Logic
- 5v Logic Level control
- PDFN5X6 SMD Package

BVDSS	30	V
ID	112	A
RDSON@VGS=10V	1.8	mΩ
RDSON@VGS=4.5V	3.2	mΩ

Applications

- High Side Load Switch
- Battery Switch
- Optimized for Power Management Applications for Portable Products, such as Aeromodelling, Power bank, Brushless motor, Main board , and Others



Order Information

Product	Package	Marking	Reel Size	Reel	Carton
PTN03N120	PDFN5X6-8L	PTN03N120	13inch	5000PCS	50000PCS

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit	
Common Ratings (TC=25°C Unless Otherwise Noted)				
V _{(BR)DSS}	Drain-Source Breakdown Voltage	30	V	
V _{GS}	Gate-Source Voltage	±20	V	
T _J	Maximum Junction Temperature	150	°C	
T _{STG}	Storage Temperature Range	-55 to 150	°C	
I _S	Diode Continuous Forward Current	TC =25°C	112	A
Mounted on Large Heat Sink				
E _{AS}	Avalanche Energy, Single Pulsed (Note1)	144	mJ	
I _{DM}	Pulse Drain Current Tested (Silicon Limit) (Note2)	TC =25°C	448	A
I _D	Continuous Drain current	TC =25°C	112	A
P _D	Maximum Power Dissipation	TC =25°C	56	W
R _{θJC}	Thermal Resistance Junction-to-Case (Note3)	2.23	°C/W	



30V/112A N-Channel Advanced Power MOSFET

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain- Source Breakdown Voltage	VGS=0V ID=250μA	30	--	--	V
I _{DSS}	Zero Gate Voltage Drain current	VDS=24V,VGS=0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	VDS=VGS,ID=250μA	1.0	1.5	2.5	V
R _{DS(ON)}	Drain-Source On-State Resistance (Note4)	VGS=10V, ID=20A	--	1.8	2.8	mΩ
		VGS=4.5V, ID=10A	--	3.2	5	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated) (Note5)						
C _{iss}	Input Capacitance	VDS=15V, VGS=0V, F=1MHz	--	3380	--	pF
C _{oss}	Output Capacitance		--	474	--	pF
C _{rss}	Reverse Transfer Capacitance		--	427	--	pF
Q _g	Total Gate Charge	VDS=15V, ID=30A, VGS=10V	--	56	--	nC
Q _{gs}	Gate-Source Charge		--	10	--	nC
Q _{gd}	Gate-Drain Charge		--	14	--	nC
Switching Characteristics (Note5)						
t _{d(on)}	Turn-on Delay Time	VDS=15V, ID=30A, RG=3Ω, VGS=10V	--	25	--	nS
t _r	Turn-on Rise Time		--	23	--	nS
t _{d(off)}	Turn-off Delay Time		--	73	--	nS
t _f	Turn-off Fall Time		--	22	--	nS
Source- Drain Diode Characteristics @ T_J = 25°C (unless otherwise stated)						
V _{SD}	Forward on voltage	IS=30A,VGS=0V	--	0.8	1.2	V
t _{rr}	Reverse Recovery Time	T _J =25°C,ISD=20A, VGS=0Vdi/dt=100A/μs	--	30	--	nS
Q _{rr}	Reverse Recovery Charge		--	15	--	nC

Note:

- Limited by T_{Jmax}, starting T_J = 25° C, RG = 4.5Ω, VD =15V, VGS =10V. Part not recommended for use above this value.
- Repetitive Rating: Pulse width limited by maximum junction temperature.
- Surface Mounted on FR4 Board, t ≤ 10 sec.
- Pulse Test: pulse width ≤ 300 us, duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.



30V/112A N-Channel Advanced Power MOSFET

Typical Characteristics

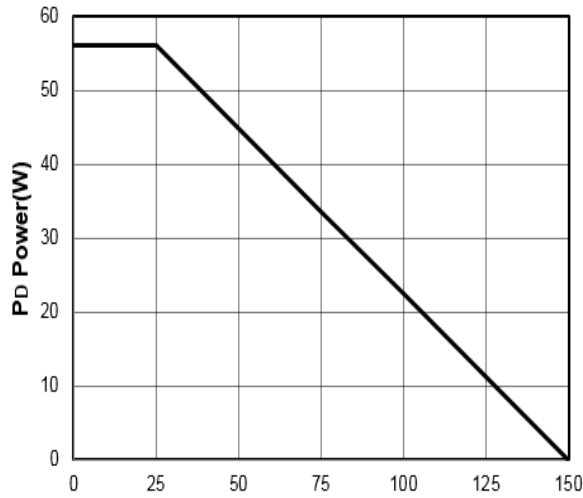


Figure1: T_J Junction Temperature (°C)

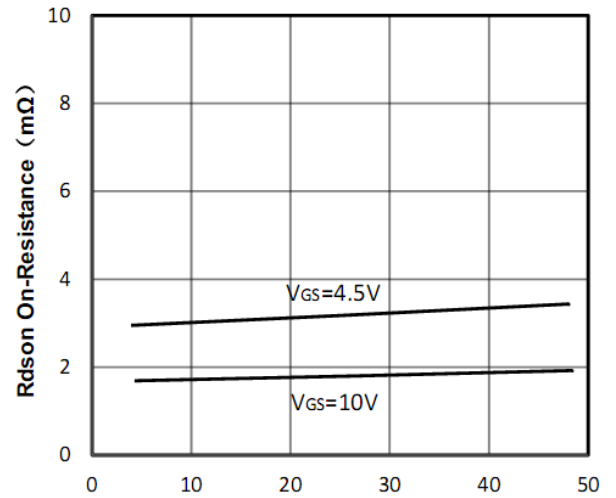


Figure2: I_D Drain Current (A)

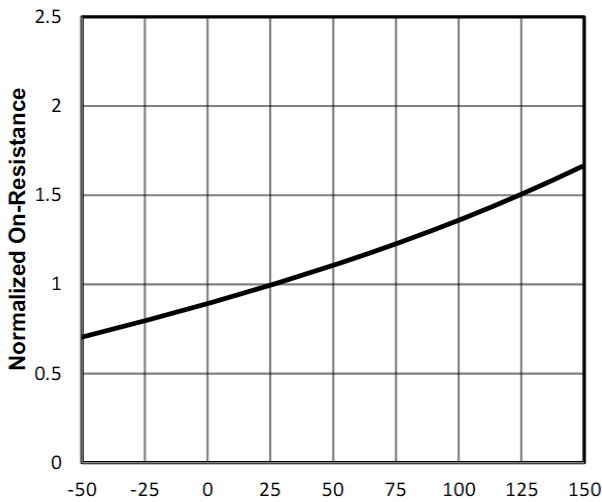


Figure3: T_J Junction Temperature (°C)

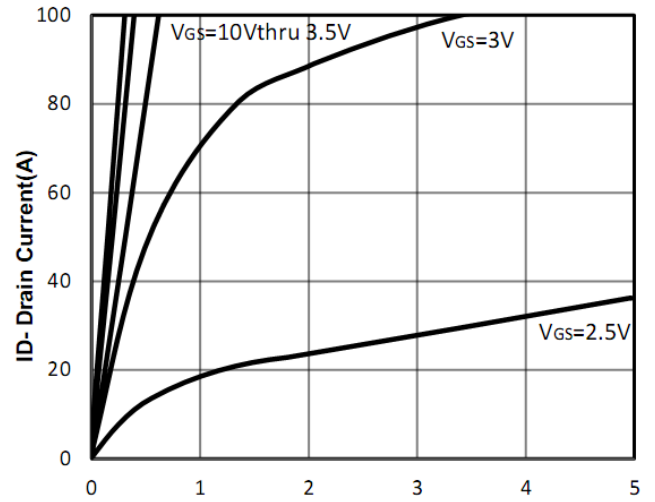


Figure4: V_{DS} Drain-Source Voltage (V)

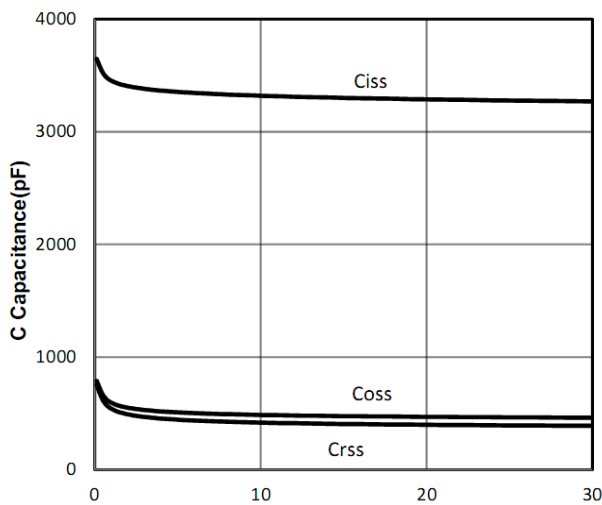


Figure5: V_{DS} Drain-Source Voltage (V)

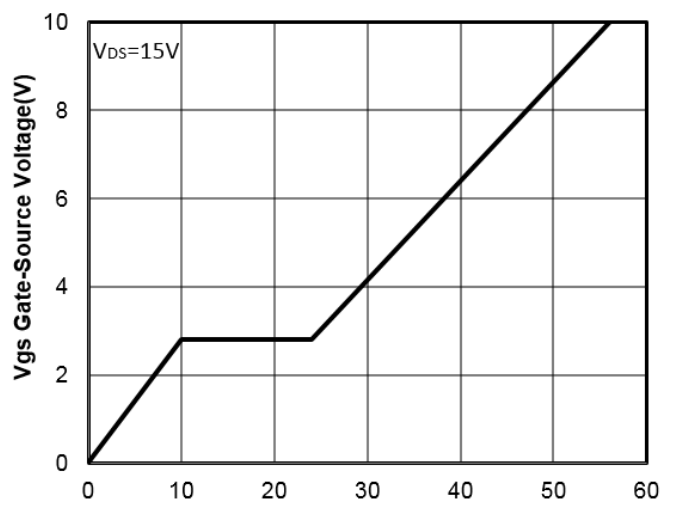


Figure6: Q_g Gate Charge (nC)



30V/112A N-Channel Advanced Power MOSFET

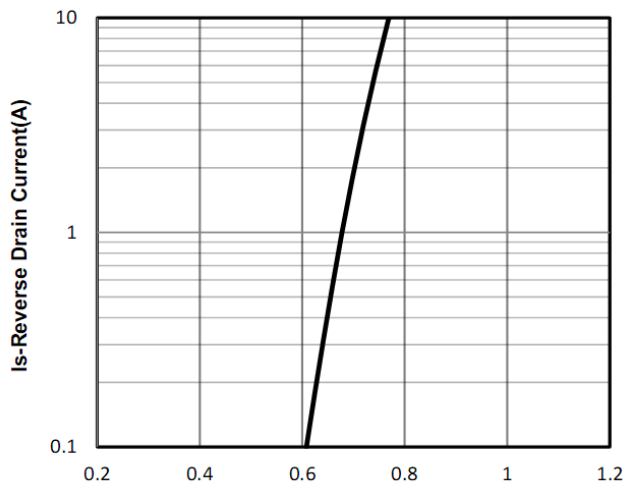


Figure7: Vsd Source-Drain Voltage (V)

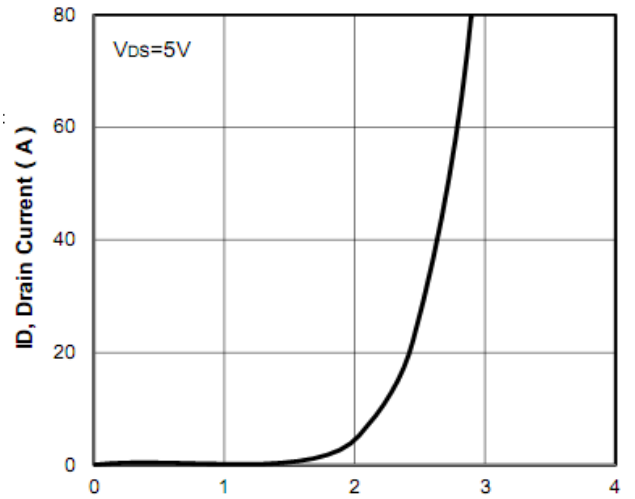


Figure8: Vgs Gate-Source Voltage (V)

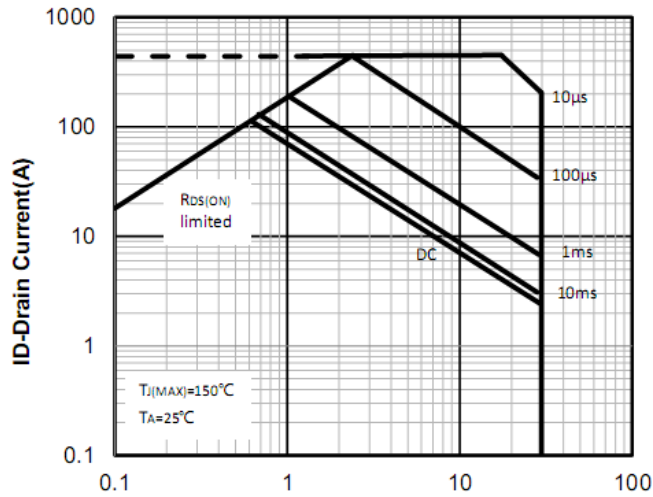


Figure9: VDS Drain -Source Voltage (V)

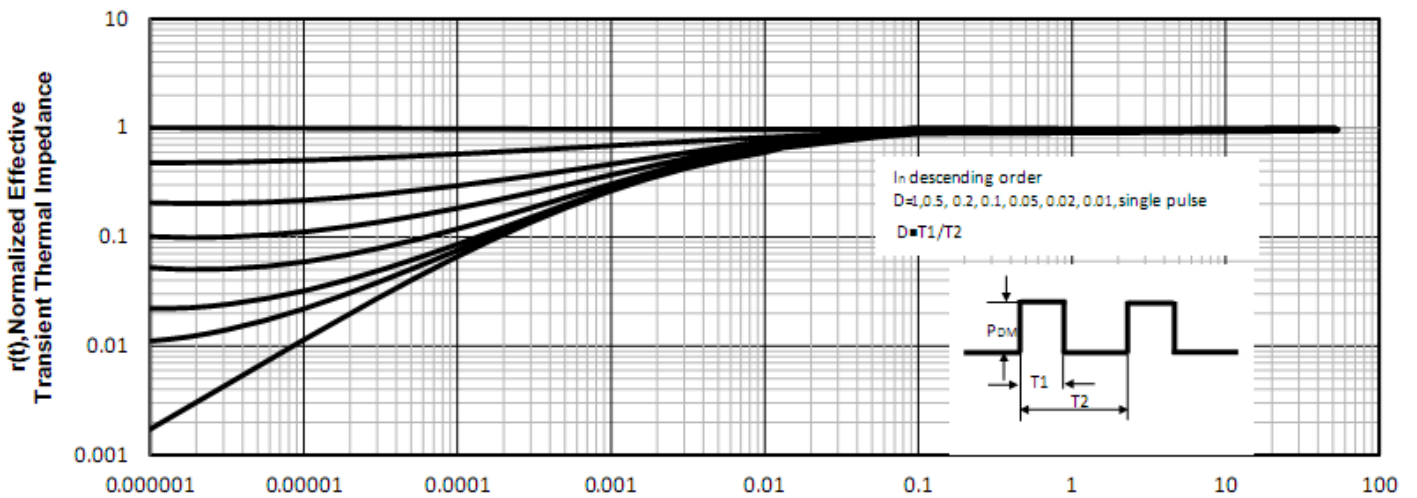
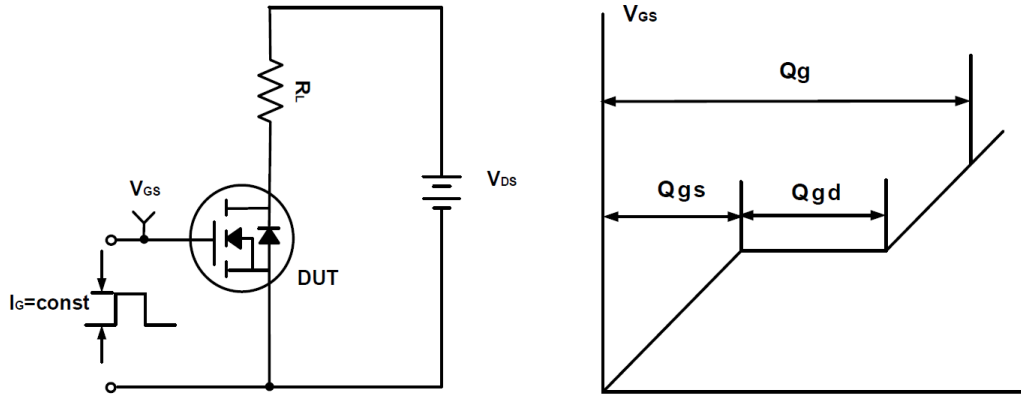
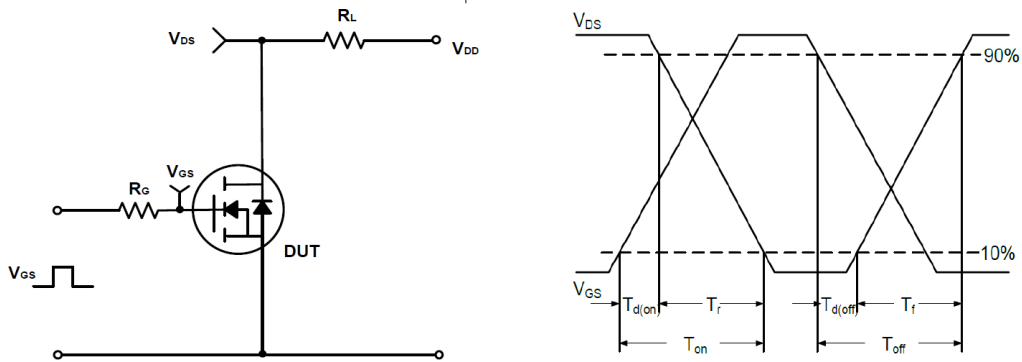
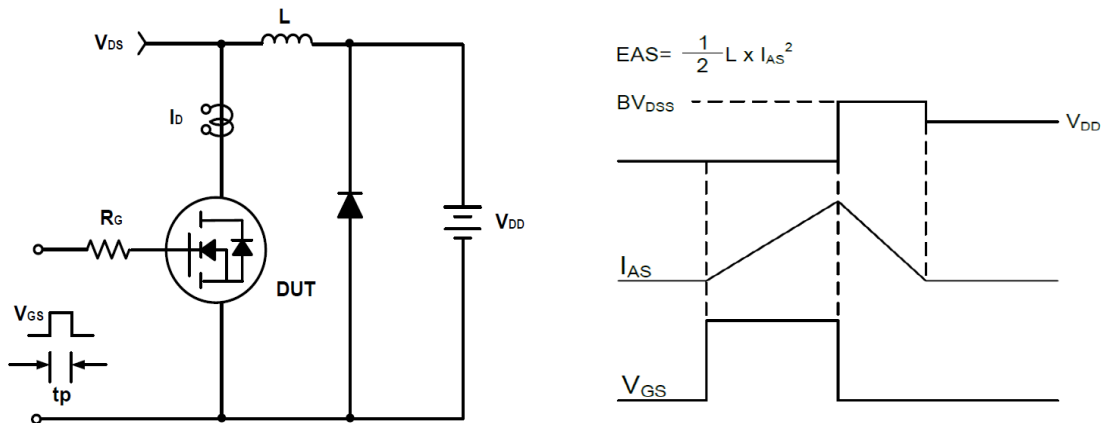
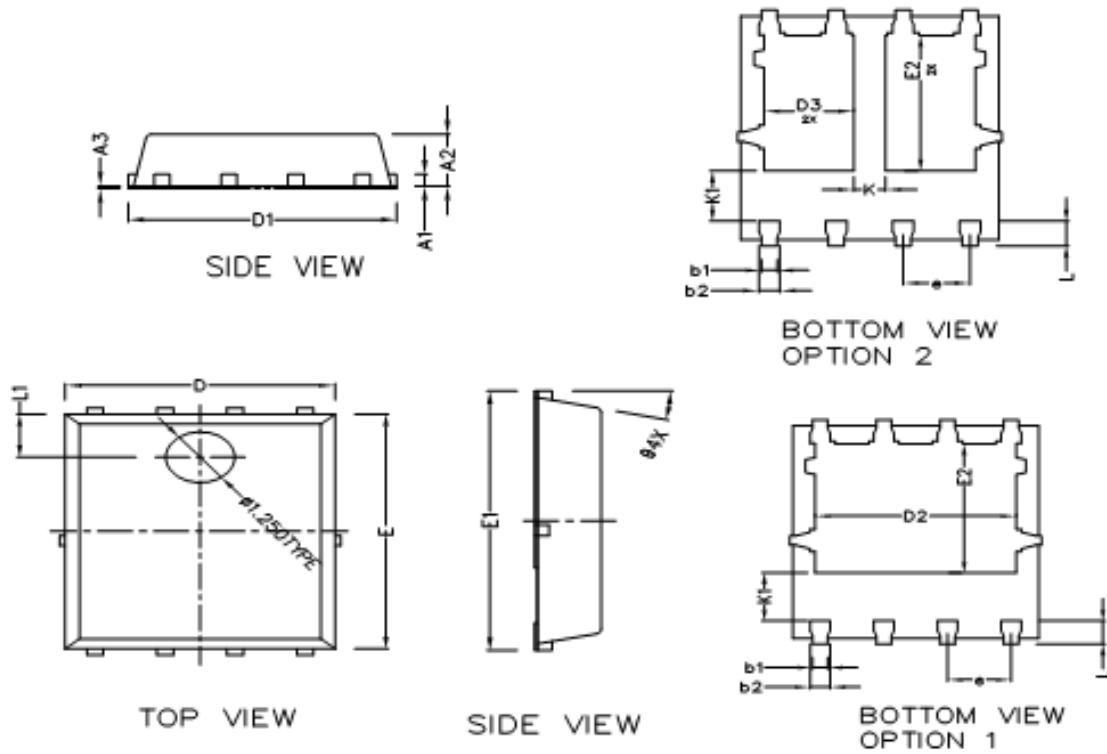


Figure10: Square Wave Pulse Duration (sec)

30V/112A N-Channel Advanced Power MOSFET
Test Circuit and Waveform:

Figure A Gate Charge Test Circuit & Waveforms

Figure B Switching Test Circuit & Waveforms

Figure C Unclamped Inductive Switching Circuit & Waveforms

30V/112A N-Channel Advanced Power MOSFET

PDFN5X6-8L Package Outline Dimensions (Units: mm)



COMMON DIMENSIONS (UNITS OF MEASURE IS mm)			
	MIN	NORMAL	MAX
A1	0.254 BSC		
A2	1.000	1.100	1.200
A3	0.005	-	0.020
b1	0.250	0.300	0.350
b2	0.350	0.400	0.450
D	4.800	4.900	5.000
D1	5.000	5.100	5.200
D2	3.910	4.010	4.110
D3	1.605	1.705	1.805
E	5.650	5.750	5.850
E1	5.950	6.050	6.150
E2	3.375	3.475	3.575
e	1.270 TYPE		
L	0.530	0.630	0.730
L1	1.00REF		
theta	13° TYPE		
K	0.600 REF		
K1	1.235 REF		